PCN Number:	PCN20121105004A	PCN Date:	1/27/2014
Title:	Qualification of DMOS5 as an additional Fab source for select devices in the LBC7 Process.		
Customer Contact:	PCN Manager	Phone: +1(214)480-6037	Dept: Quality Services
Proposed 1st Ship Date:	N/A	Estimated Sample Availability:	Date provided at sample request.

Change Type:					
☐	Assembly Site	☐	Assembly Process	☐	Assembly Materials
☐	Design	☐	Electrical Specification	☐	Mechanical Specification
☐	Test Site	☐	Packing/Shipping/Labeling	☐	Test Process
☐	Wafer Bump Site	☐	Wafer Bump Material	☐	Wafer Bump Process
☒	Wafer Fab Site	☐	Wafer Fab Materials	☐	Wafer Fab Process

PCN Details

Description of Change:

The purpose of Rev A is to cancel the addition of DMOS5 as an additional Fab source for select devices in the LBC7 Fab Process. Affected devices will remain in their current location.

This change notification is to announce DMOS5 as an additional Fab source for select devices in the LBC7 Fab Process. These devices are listed in "Product Affected" section.

Currently Qualified Site, Process	~~**Additional Site, Process**~~
MIHO8, LBC7 Process	~~**DM5, LBC7 Process**~~

The LBC7 process was previously qualified at DMOS5 on 2/16/2007. The affected devices are being qualified by similarity. Qualification details are shown in the Qual Data Section of this document.

Reason for Change:

Continuity of Supply

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

There is no change to the product quality or reliability. All current product specifications, performance parameters and characteristics will remain unchanged. The expectation is that there will not be an effect on customer applications.

Changes to product identification resulting from this PCN:

Current

Chip Site	Chip site code (20L)	Chip country code (21L)
MIHO8	MH8	JPN

New

~~Chip Site~~	~~Chip site code (20L)~~	~~Chip country code (21L)~~
~~**DP1DM5**~~	~~**DM5**~~	~~**USA**~~

Sample product shipping label (not actual product

label

Product Affected:			
~~TPS2000CDGK~~	~~TPS2051CDBVT~~	~~TPS2064CDGN~~	~~TPS2066CDGNR~~
~~TPS2000CDGKR~~	~~TPS2052CDGN~~	~~TPS2064CDGN-2~~	~~TPS2066CDGNR-2~~
~~TPS2000CDGN~~	~~TPS2052CDGNR~~	~~TPS2064CDGNR~~	~~TPS2066CDR~~
~~TPS2000CDGNR~~	~~TPS2060CDGN~~	~~TPS2064CDGNR-2~~	~~TPS2068CDGN~~
~~TPS2001CDGK~~	~~TPS2060CDGNR~~	~~TPS2065CDBVR~~	~~TPS2068CDGNR~~
~~TPS2001CDGKR~~	~~TPS2061CDBVR~~	~~TPS2065CDBVR-2~~	~~TPS2069CDBVR~~
~~TPS2001CDGN~~	~~TPS2061CDBVT~~	~~TPS2065CDBVT~~	~~TPS2069CDBVT~~
~~TPS2001CDGNR~~	~~TPS2061CDGN~~	~~TPS2065CDBVT-2~~	~~TPS2069CDGK~~
~~TPS2002CDRCR~~	~~TPS2061CDGNR~~	~~TPS2065CDGN~~	~~TPS2069CDGKR~~
~~TPS2002CDRCT~~	~~TPS2062CD~~	~~TPS2065CDGN-2~~	~~TPS2069CDGN~~
~~TPS2003CDRCR~~	~~TPS2062CDGN~~	~~TPS2065CDGNR~~	~~TPS2069CDGN-2~~
~~TPS2003CDRCT~~	~~TPS2062CDGNR~~	~~TPS2065CDGNR-2~~	~~TPS2069CDGNR~~
~~TPS2041CDBVR~~	~~TPS2062CDR~~	~~TPS2066CD~~	~~TPS2069CDGNR-2~~
~~TPS2041CDBVT~~	~~TPS2062CDRBR-2~~	~~TPS2066CDGN~~	~~TPS2530DBVR~~
~~TPS2051CDBVR~~	~~TPS2062CDRBT-2~~	~~TPS2066CDGN-2~~	~~TPS2530DBVT~~

Reference Qualification (LBC7 Wafer Process in DMOS5)

Qualification Data: (Approved 2/16/2007)			
This qualification has been specifically developed for the validation of this change. The qualification data validates that the proposed change meets the applicable released technical specifications.			
Qual Vehicle 1: BQ24721RHB (MSL3-260C)			
Package Construction Details			
Wafer Fab Site:	DMOS5	Wafer Fab Process:	LBC7
Wafer Diameter:	200mm	Metallization:	TiN/AlCu.5/TiN
Passivation:	10KACN		

Qualification: ☐ **Plan** ☒ **Test Results**				
Reliability Test	Conditions	Sample Size / Fails		
		Lot 1	Lot2	Lot 3
**Temp Cycle	-65C/+150C (1000 Cycles)	77/0	77/0	77/0
**Autoclave	121C (240 Hrs)	77/0	77/0	77/0
**Thermal Shock	-65C/150C (1000 Cycles)	77/0	77/0	77/0
**High Temp. Storage Bake	170C (420 Hrs)	77/0	77/0	77/0
ESD HBM	2000V	3/0	3/0	3/0
ESD CDM	500V	3/0	3/0	3/0
Latch-up	Per JESD78	5/0	5/0	5/0
Electrical Characterization	Per Site Specification	Pass	Pass	Pass
Wafer Level Reliability	Per Site Specification	Pass	Pass	Pass
Manufacturability	Per Site Specification	Pass	Pass	-
**Preconditioning sequence: MSL3-260C				

Qual Vehicle 2: BQ24730RGF (MSL3-260C)			
Wafer Fab Site:	DMOS5	Wafer Fab Process:	LBC7
Wafer Diameter:	200mm	Metallization:	TiN/AlCu.5/TiN
Passivation:	10KACN		

Qualification: ☐ **Plan** ☒ **Test Results**				
Reliability Test	Conditions	Sample Size / Fails		
		Lot 1	Lot2	Lot 3
**Life Test	155C (240 Hrs)	116/0	116/0	116/0
Early Life Failure Rate	155C (48 Hrs)	611/0	611/0	611/0
Electrical Characterization	Per Site Specification	Pass	Pass	Pass
Manufacturability	Per Site Specification	Pass	Pass	-
Wafer Level Reliability	Per Site Specification	Pass	-	-
**Preconditioning sequence: MSL3-260C				

Qual Vehicle 3: SH6964BBA0G4 (MSL3-260C)			
Wafer Fab Site:	DMOS5	Wafer Fab Process:	LBC7
Wafer Diameter:	200mm	Metallization:	TiN/AlCu.5/TiN
Passivation:	10KACN		

Qualification: ☐ **Plan** ☒ **Test Results**				
Reliability Test	Conditions	Sample Size / Fails		
		Lot 1	Lot2	Lot 3
**HAST	130C/85%RH (96 Hrs)	77/0	77/0	77/0
Wafer Level Reliability	Per Site Specification	Pass	-	-
Manufacturability	Per Site Specification	Pass	-	-
**Preconditioning sequence: MSL3-260C				

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	**E-Mail**
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com